

# OPTICAL PERFORMANCE OF HIGH TEMPERATURE AIR-STABLE SOLAR ABSORBER COATINGS BASED ON W/SiCH PLASMA MULTILAYERS

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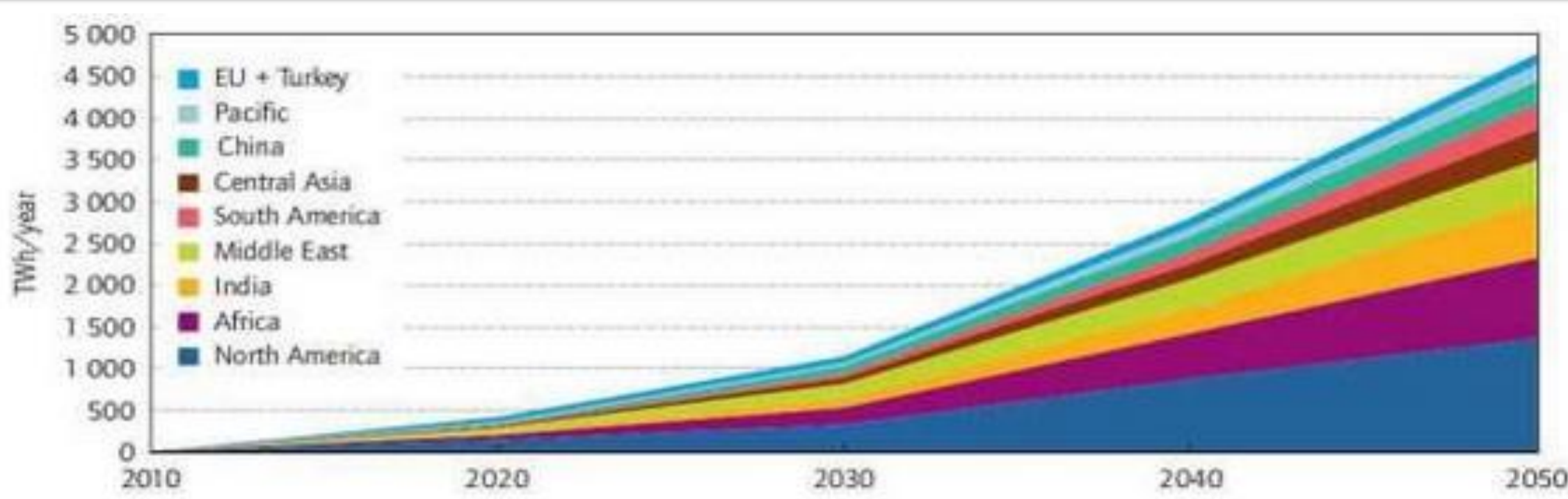
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## Context : Concentrated Solar Power

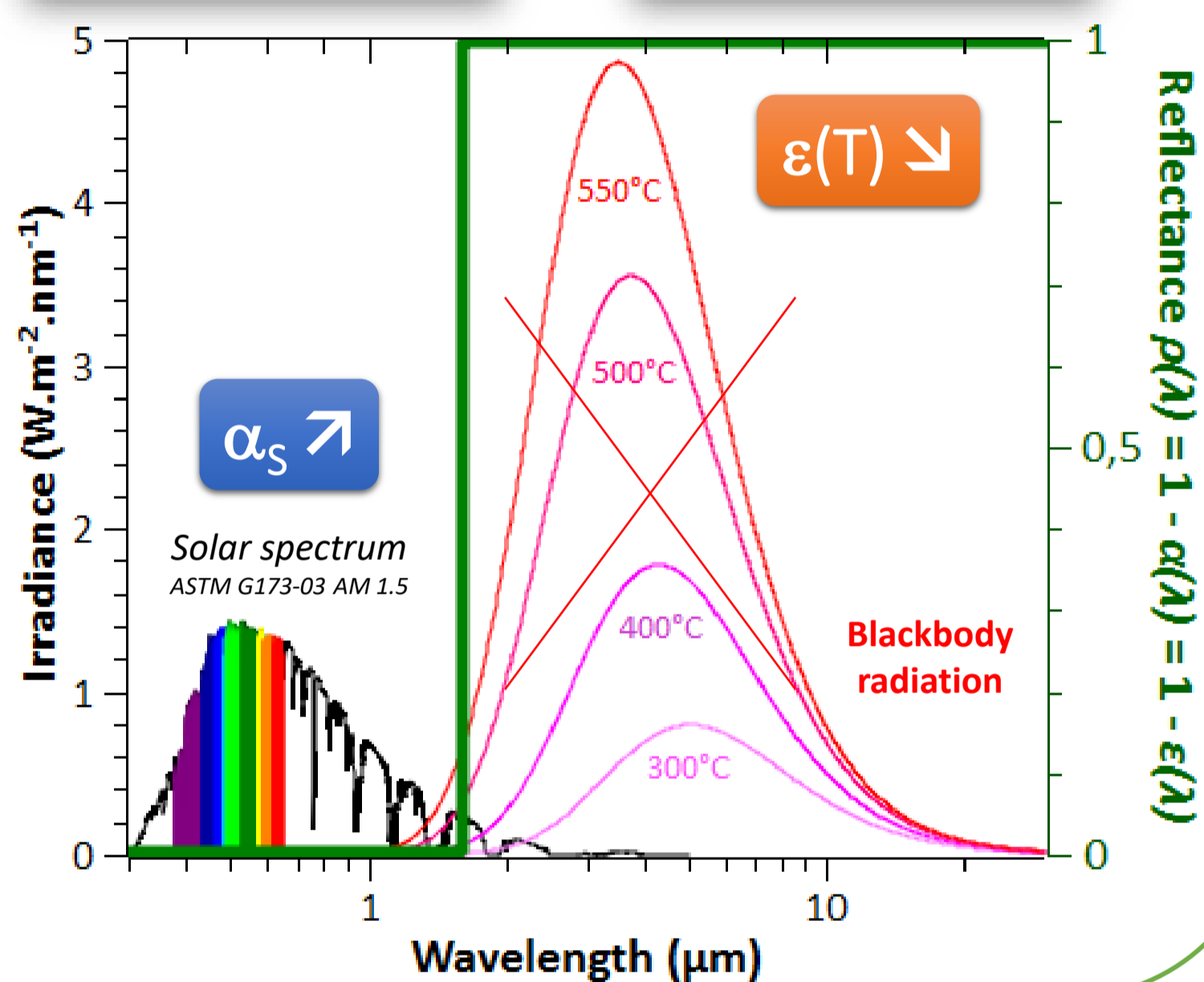


CSP 2050 projections in the world



For an ideal solar receiver, spectral reflectance  $\rho(\lambda)$

- is low in solar range
- is high in IR range
- increases steeply at  $\lambda_{cutoff} \approx 1.5 - 2 \mu\text{m}$  (depends on  $T$ )



## W/SiCH periodic bilayer absorbers

All solar receivers need **high optical performance**

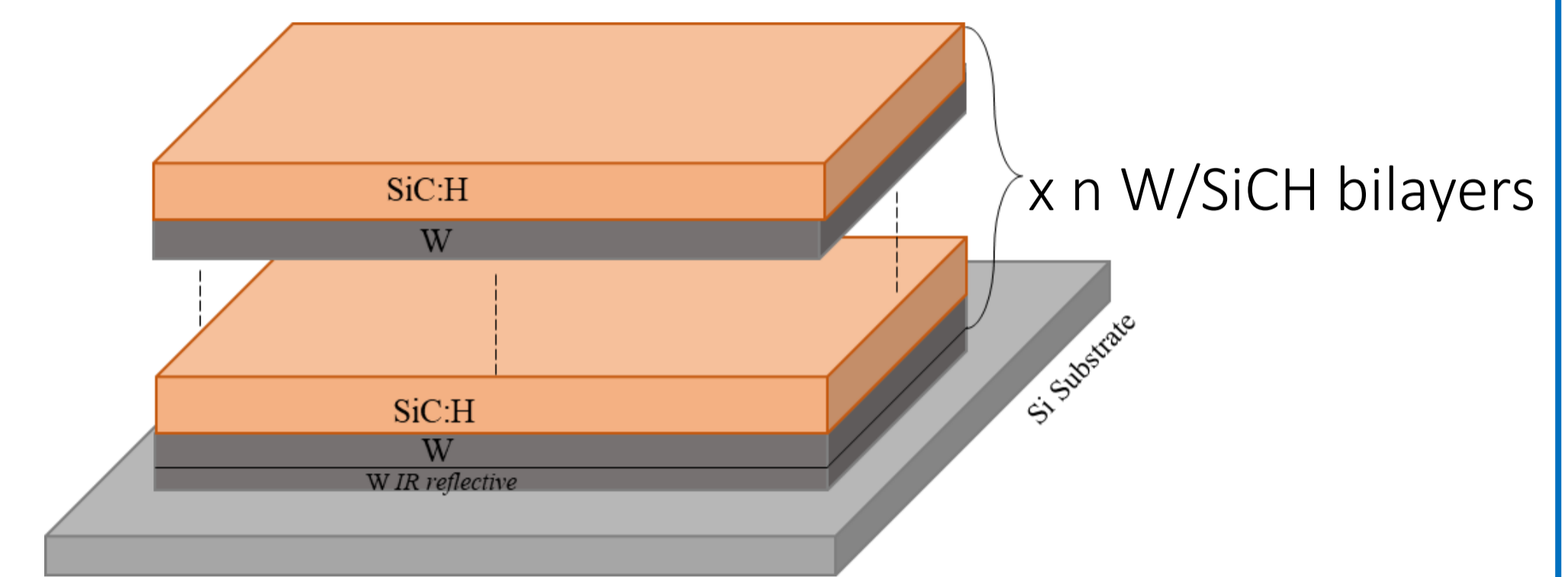
- High solar absorptance  $\alpha_s$  to increase absorbed solar input  $\alpha_s C I$
- Low thermal emittance  $\epsilon(T)$  to limit radiative thermal losses  $\epsilon(T) \sigma T^4$
- High solar-to-heat conversion (heliothermal) efficiency

$$\eta(T) = \alpha_s - \frac{\epsilon(T) \cdot \sigma(T^4 - T_0^4)}{C \cdot I \cdot \eta_{opt}}$$

→ Metallic pipes covered with **Solar Selective Absorber Coatings**

New generations also need **high thermal stability/durability in air**

- i.e. resistance or adaptation for long durations to:
- high temperatures  $> 500^\circ\text{C}$  → oxidation, atomic diffusion, etc.
- high thermomechanical stress & thermal shocks → fatigue, creep, etc.
- concentrated solar irradiance



**SiCH** : dielectric

- HT stability ( $T_r = 1400^\circ\text{C}$ )
- variable optical indices

**W** : metal

- Resistant = HT stability ( $T_r = 3400^\circ\text{C}$ )
- IR reflective

### Deposition technique



Vacuum plasma reactor

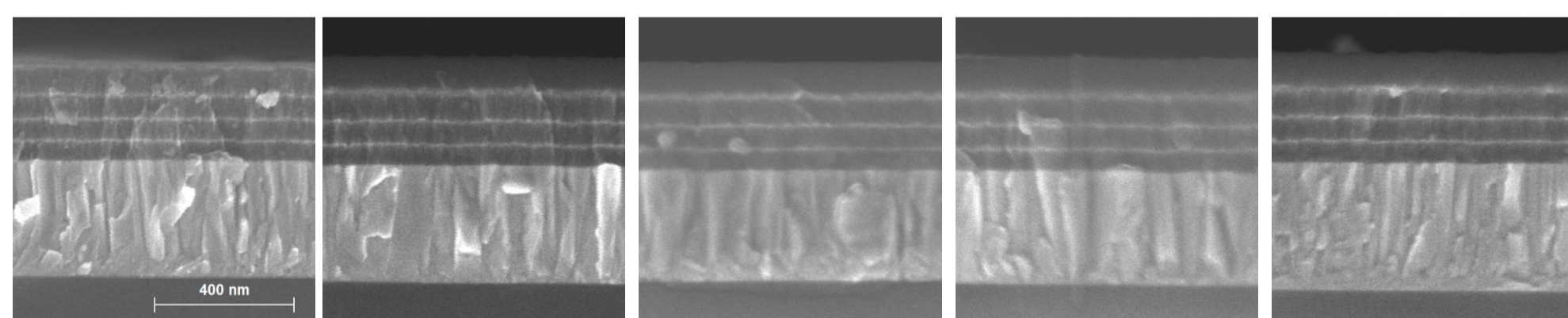
- SiCH: PECVD
- W: PVD (sputtering)

## Optical Performance and Thermal stability

- 5 equivalent samples (S1-S5) annealed for up to 96h at  $500^\circ\text{C}$  in air with  $n = 4$  W/SiCH bilayers

### SEM cross-section images / EDS composition

- 4 bilayers remain visible, slight increase in top layer thickness
- Increase in at.% O content



S1 as-deposited 1 at.% O  
S2 annealed 12h 18 at.% O  
S3 annealed 24h 24 at.% O  
S4 annealed 48h 16 at.% O  
S5 annealed 96h 12 at.% O

### Optical performance: $\alpha_s \nearrow$ , $\epsilon(500^\circ\text{C}) \searrow$ , $\eta_{heliotherm} \nearrow$

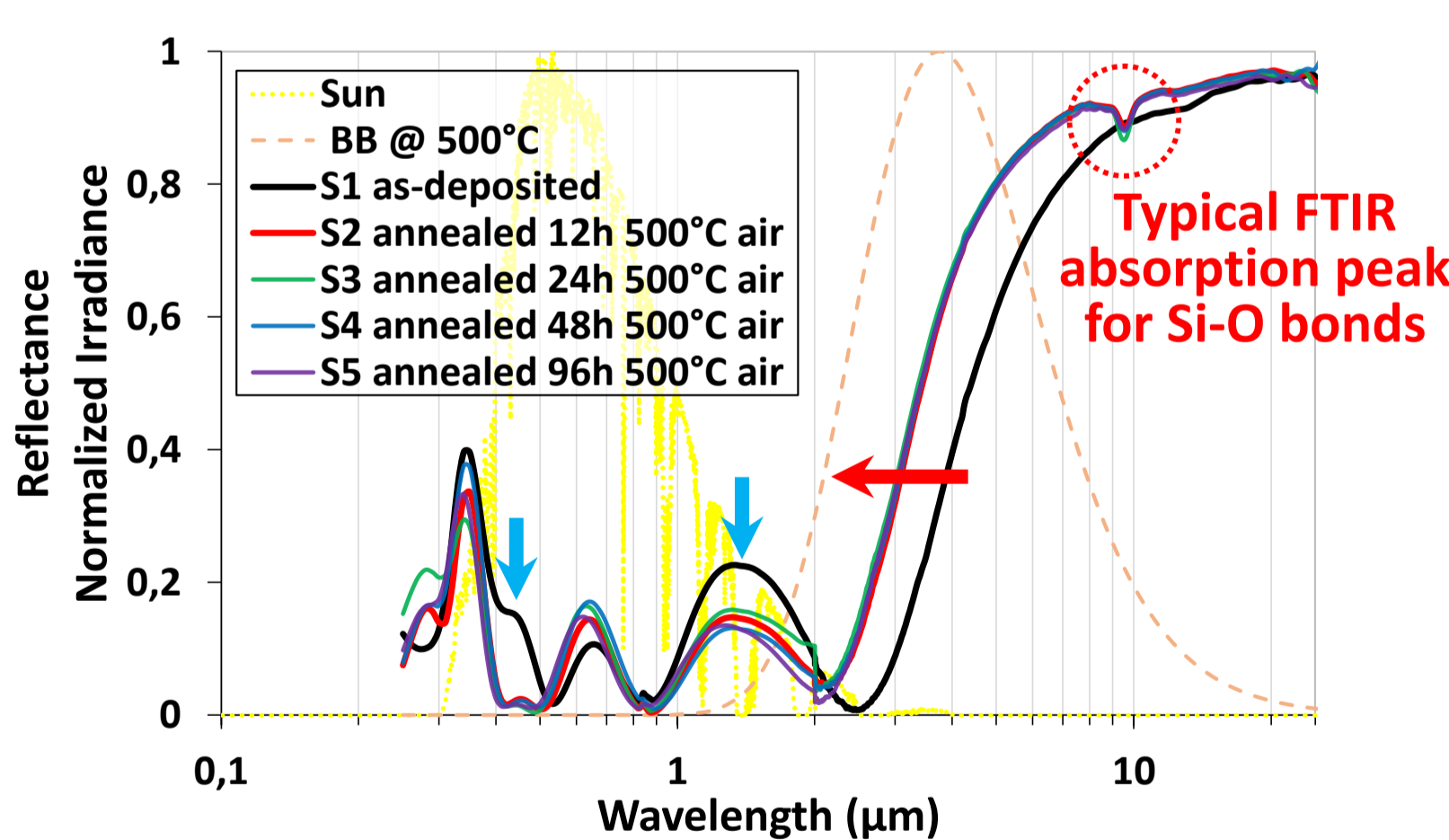
Samples	$\alpha_s$	$\epsilon(500^\circ\text{C})$	$\eta_{heliotherm}^*$	$\Delta\alpha_s$	$\Delta\epsilon$	$\Delta\eta$
S1-S5 as-deposited	0.896	0.426	0.521	-	-	-
S2 annealed 12h	$\pm 0.001$	$\pm 0.007$	$\pm 0.006$	0.023	-0.141	0.148
S3 annealed 24h	0.912	0.280	0.666	0.016	-0.146	0.145
S4 annealed 48h	0.913	0.286	0.661	0.016	-0.152	0.150
S5 annealed 96h	0.920	0.290	0.665	0.024	-0.128	0.137

\* Calculated for  $T = 500^\circ\text{C}$ ,  $T_0 = 25^\circ\text{C}$ ,  $C = 50$ ,  $I = 900 \text{ W/m}^2$ ,  $\eta_{opt} = 0.50$

- Annealing 12h @  $500^\circ\text{C}$  in air: optical performance + stability  $\nearrow$  = curing step
- Oxidation of SiCH top layer + formation of protective/antireflective  $\text{SiO}_x$  ?

### Spectral reflectance

- Evolution after 12h:
  - %R  $\searrow$  in solar range,  $\lambda_{cutoff} \searrow$
  - absorption peak @  $9.5 \mu\text{m}$  ( $1050 \text{ cm}^{-1}$ ) → Si-O ?
- Same after 24h, 48h and 96h → stabilization



### Solar aging (SAAF PROMES)

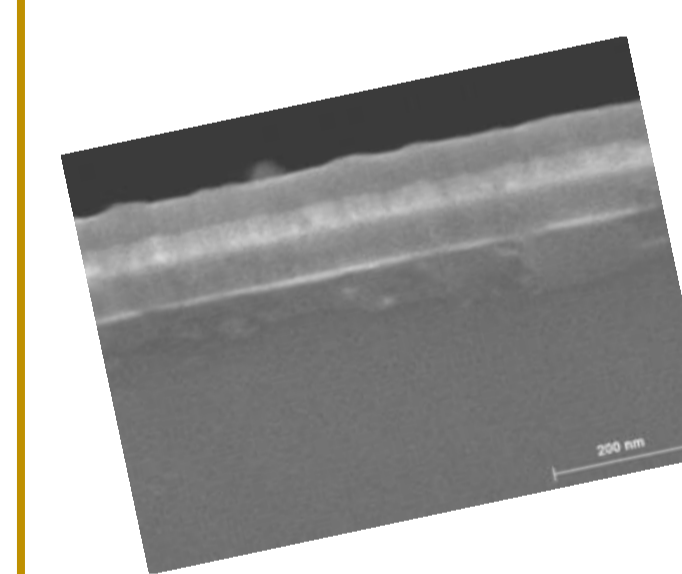


Similar trends were observed on sample exposed in solar furnace to concentrated solar irradiance [ $150 \text{ kW/m}^2$ ,  $400^\circ\text{C}$ , 1.5h]

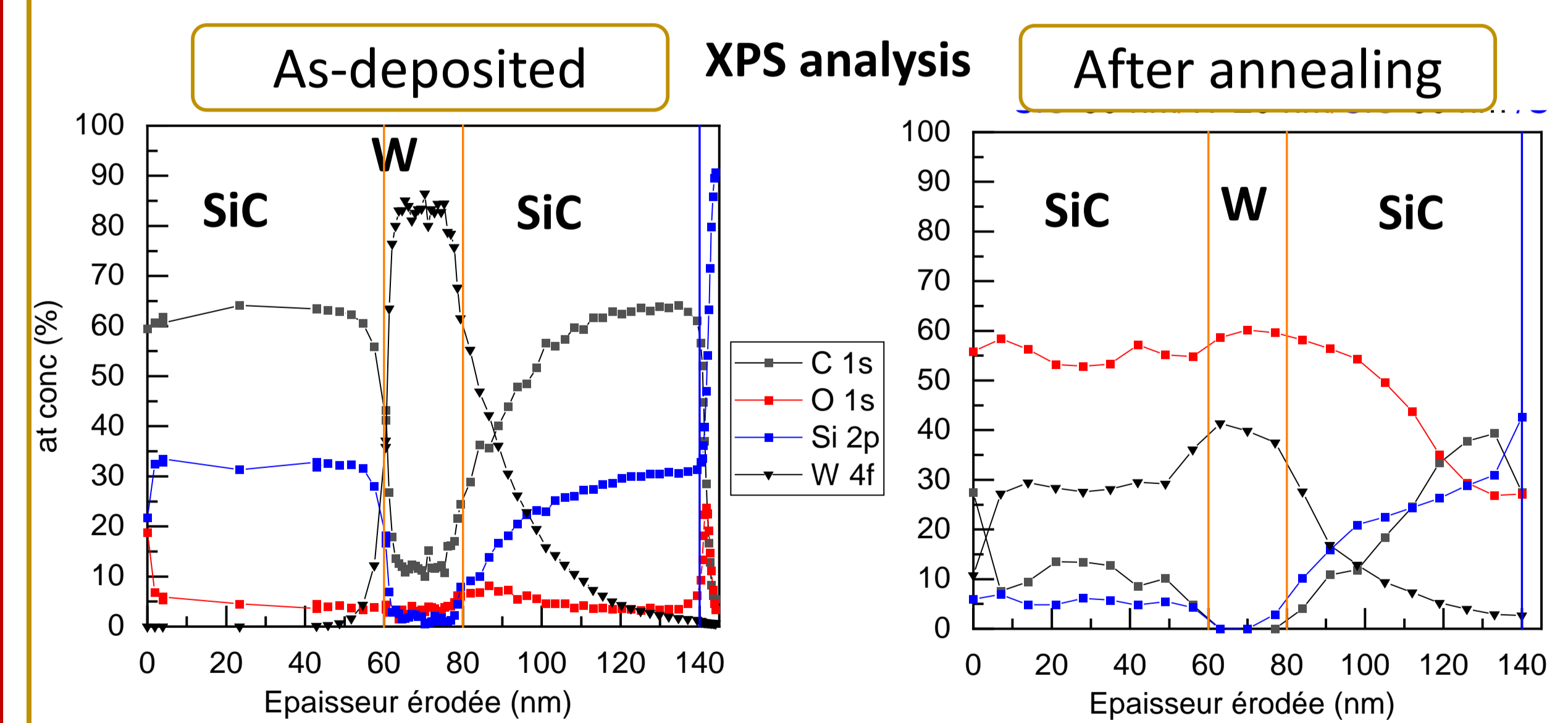
→ Evolutions due to thermally-induced aging phenomena only

- Optical perf. not affected by oxidation of all layers
- W interlayer diffusion → W-SiCH nanocomposites ?

## Diffusion phenomenon



- SiCH-W-SiCH 3-layer on Si as-deposited vs. annealed 96h  $500^\circ\text{C}$  air



RBS % O	Top layer		Bottom layer	
	As-deposited	After annealing	As-deposited	After annealing
	3,92	18,94	5,06	42,25

- W broad profile → W diffusion
- C replaced by O → oxidation

## Conclusions and further work

- Plasma deposited (W, SiCH) solar selective absorber coatings with good optical performance and thermal stability in air at  $500^\circ\text{C}$  were developed for CSP technologies.
- Annealing of periodic bilayers promotes oxidation and interlayer diffusion, thus improving and stabilizing solar performance.
- Further characterizations and aging tests are underway to investigate the evolution of the material microstructure and its oxidation/diffusion kinetics.